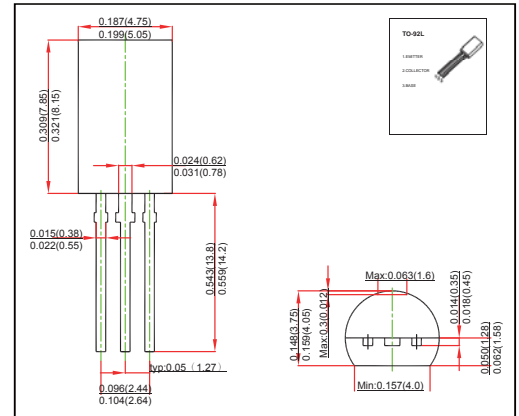


TO-92L Plastic-Encapsulate Transistors
FEATURE

- High Voltage :V_{CEO}=300V
- Small Collector Output Capacitance: Cob=3.0pF(Typ)
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style:TO-92L molded plastic
- Mounting position:any


MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	300	V
Collector-Emitter Voltage	V _{CEO}	300	V
Emitter-Base Voltage	V _{EBO}	7	V
Collector Current -Continuous	I _C	0.1	A
Collector Power Dissipation	P _C	0.9	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55~+150	°C

ELECTRICAL CHARACTERISTICS T_A =25 °C unless otherwise specified

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR) _{CBO}	I _C = 100μA, I _E =0	300			V
Collector-emitter breakdown voltage	V(BR) _{CEO}	I _C = 3mA, I _B =0	300			V
Emitter-base breakdown voltage	V(BR) _{EBO}	I _E = 100μA, I _C =0	7			V
Collector cut-off current	I _{CBO}	V _{CB} =240V, I _E =0			1.0	μA
Collector cut-off current	I _{CEO}	V _{CB} =240V, I _B =0			5.0	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 7V, I _C =0			1.0	μA
DC current gain	h _{FE}	V _{CE} =10V, I _C =20mA	30		150	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =10mA, I _B =1mA			1.0	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =10mA, I _B =1mA			1.0	V
Transition frequency	f _T	V _{CE} =10V, I _C =20mA, f=30MHz	50			MHz
Collector output capacitance	Cob	V _{CB} =20V, I _E =0, f=1MHz		3		pF